IXYS Advance Technical Information

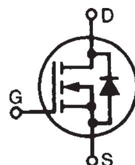
High Voltage Power MOSFET

IXTF1N250

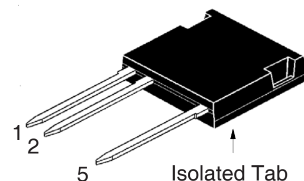
V_{DSS} = 2500V
I_{D25} = 1A
$R_{DS(on)}$ ≤ 40Ω

N-Channel Enhancement Mode

(Electrically Isolated Tab)



ISOPLUS i4-Pak™



1 = Gate 5 = Drain
2 = Source

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	2500	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	2500	V
V_{GSS}	Continuous	±20	V
V_{GSM}	Transient	±30	V
I_{D25}	T_C = 25°C	1	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	6	A
P_D	T_C = 25°C	110	W
T_J		- 55 ... +150	°C
T_{JM}		150	°C
T_{stg}		- 55 ... +150	°C
T_L	1.6mm (0.062 in.) from Case for 10s	300	°C
T_{SOLD}	Plastic Body for 10s	260	°C
M_d	Mounting Force	20..120 / 4.5..27	Nm/lb.in.
V_{ISOL}	50/60Hz, 1min	2500	V~
Weight		5	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 250µA	2500			V
$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250µA	2.0		4.0	V
I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
I_{DSS}	V_{DS} = 0.8 • V_{DSS}, V_{GS}= 0V			25	µA
	Note 2, T_J = 125°C		25		µA
$R_{DS(on)}$	V_{GS} = 10V, I_D = 0.5 • I_{D25}, Note 1			40	Ω

Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 2500V Electrical Isolation
- Molding Epoxies meet UL 94 V-0 Flammability Classification

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- High Voltage Power Supplies
- Capacitor Discharge
- Pulse Circuits

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Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Min.	Typ.	Max.	
g_{fs}	V_{DS} = 50V, I_D = 0.5 • I_{D25}, Note 1	1.0	1.8		mS
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		1660		pF
C_{oss}			77		pF
C_{rss}			23		pF
$t_{d(on)}$	**Resistive Switching Times**		69		ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = I_{D25}		25		ns
$t_{d(off)}$	R_G = 5Ω (External)		132		ns
t_f			39		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 600V, I_D = 0.5 • I_{D25}		41		nC
Q_{gs}			8		nC
Q_{gd}			16		nC
R_{thJC}				1.13	°C/W
R_{thCS}			0.21		°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Min.	Typ.	Max.	
I_S	V_{GS} = 0V			1.5	A
I_{SM}	Repetitive, pulse width limited by T_{JM}			6	A
V_{SD}	I_F = 1A, V_{GS} = 0V, Note 1			1.5	V
t_{rr}	I_F = 1A, -di/dt = 100A/μs, V_R = 200V		2.5		μs

ISOPLUS i4-Pak™ (HV) Outline

Pin 1 = Gate
Pin 2 = Source
Pin 3 = Drain
Tab 4 = Isolated

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.190	.205	4.83	5.21
A1	.102	.118	2.59	3.00
A2	.046	.085	1.17	2.16
b	.045	.055	1.14	1.40
b1	.058	.068	1.47	1.73
C	.020	.029	0.51	0.74
D	.819	.840	20.80	21.34
E	.770	.799	19.56	20.29
e	.150 BSC		3.81 BSC	
e1	.450 BSC		11.43 BSC	
L	.780	.840	19.81	21.34
L1	.083	.102	2.11	2.59
Q	.210	.244	5.33	6.20
R	.100	.180	2.54	4.57
S	.660	.690	16.76	17.53
T	.590	.620	14.99	15.75
U	.065	.080	1.65	2.03

Notes
1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.
2. Device must be heatsunk for high-temp I_{DSS} measurement to avoid thermal runaway.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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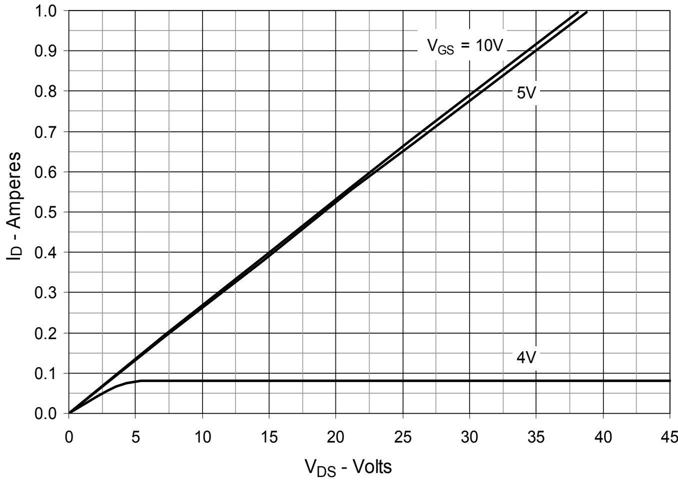
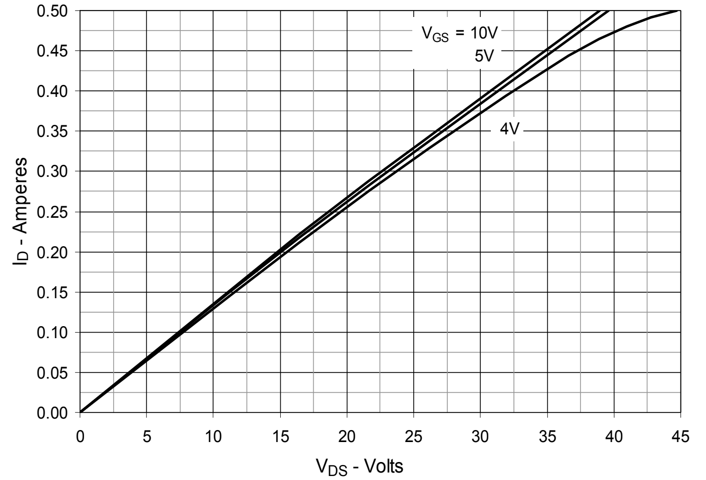
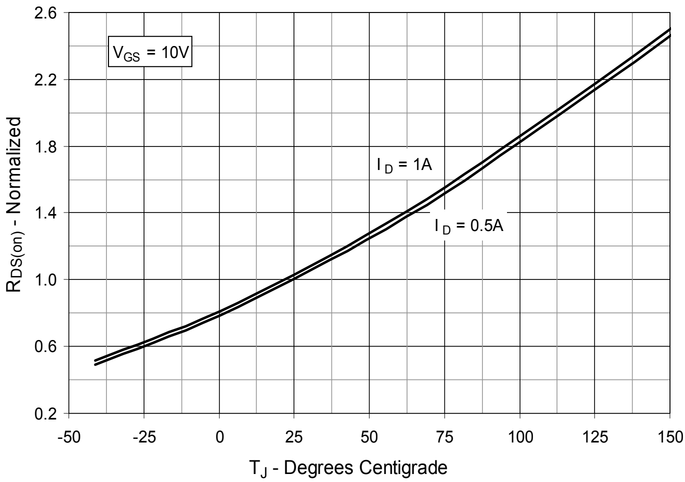
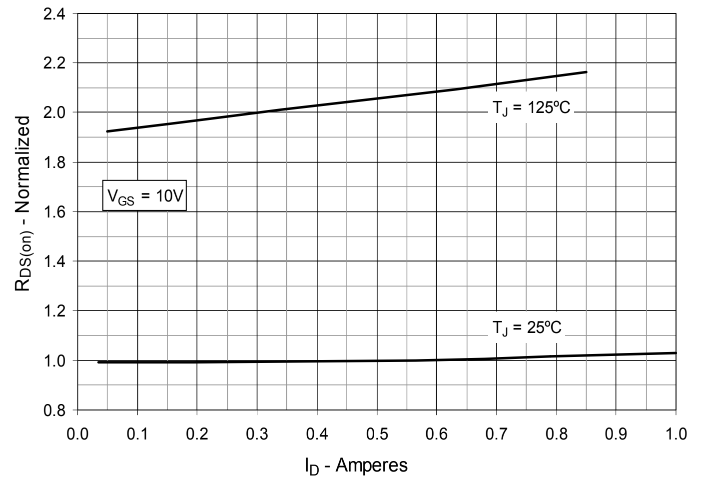
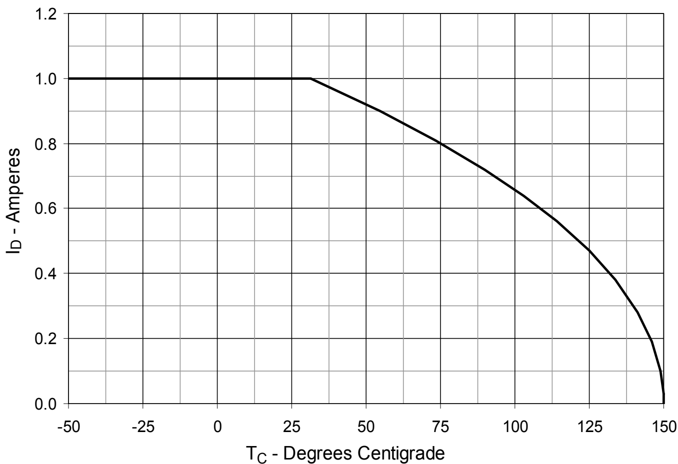
IXYS MOSFETs and IGBTs are covered by one or moreof the following U.S. patents: 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

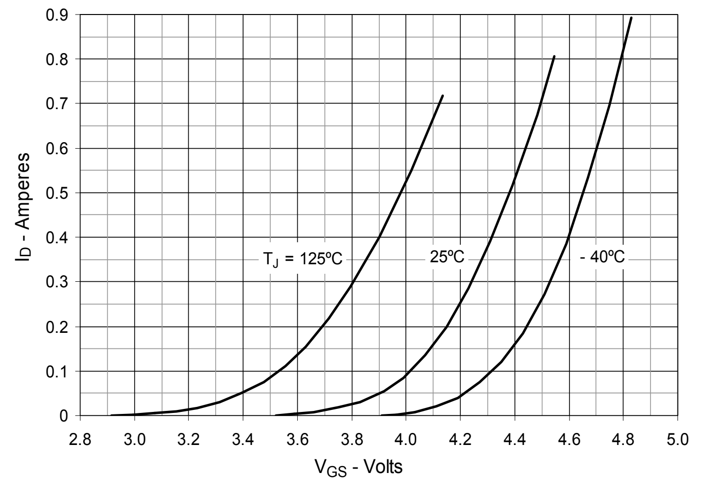












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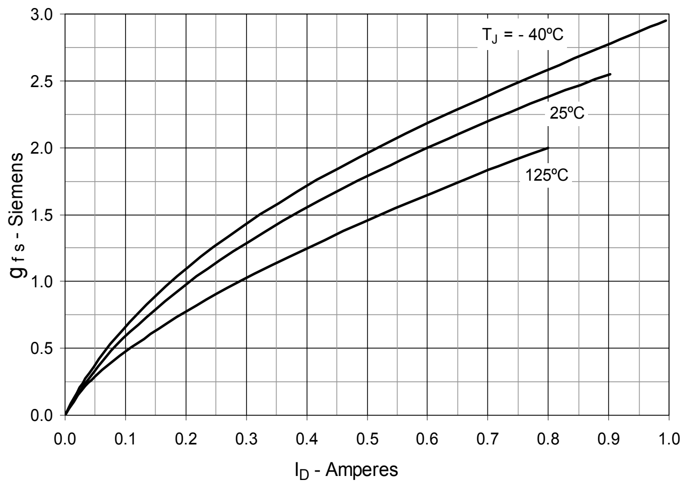

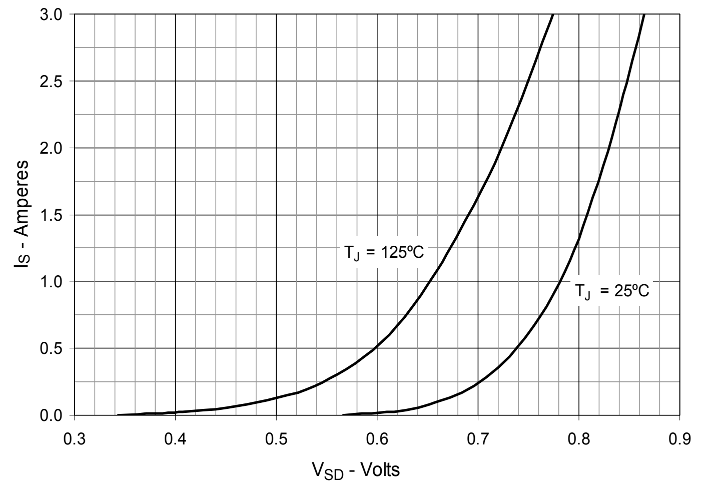

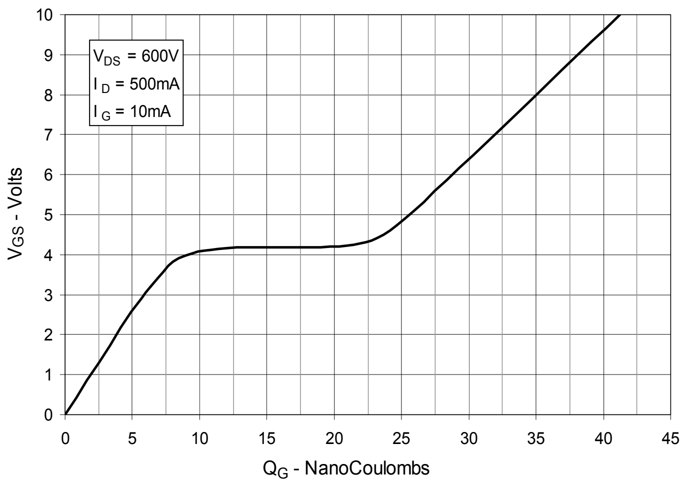

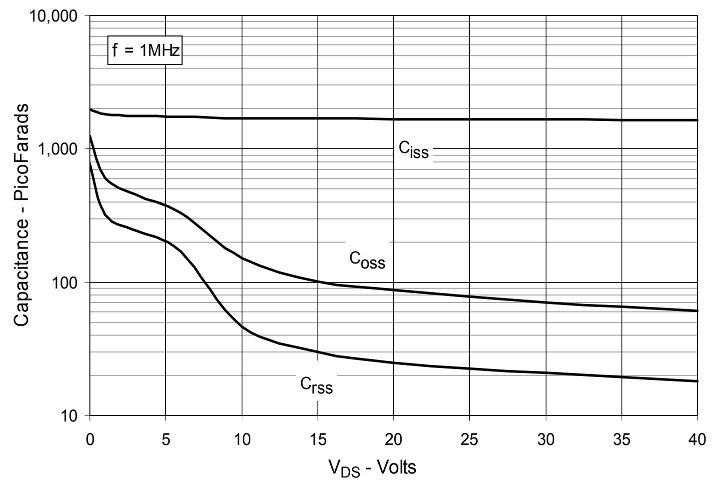

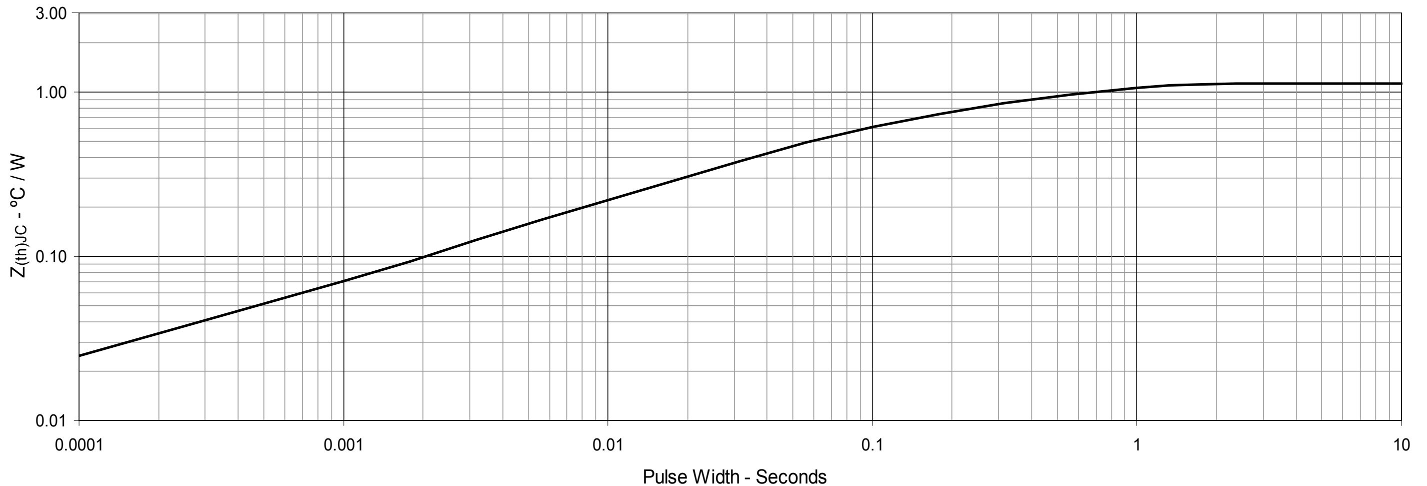

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